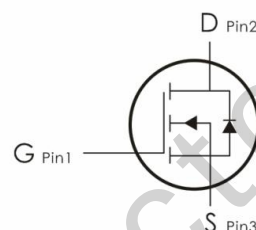


FEATURES

- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)



Device Marking and Package Information		
Device	Package	Marking
2N0609	TO-263	2N0609

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, unless otherwise noted			
Parameter	Symbol	Value	Unit
		TO-220	
Drain-Source Voltage ($V_{GS} = 0V$)	V_{DSS}	60	V
Continuous Drain Current	I_D	110	A
Pulsed Drain Current (note1)	I_{DM}	440	A
Gate-Source Voltage	V_{GSS}	± 20	V
Single Pulse Avalanche Energy (note2)	E_{AS}	653	mJ
Avalanche Current (note1)	I_{AS}	40	A
Repetitive Avalanche Energy (note1)	E_{AR}	391.8	mJ
Power Dissipation ($T_C = 25^\circ\text{C}$)	P_D	108	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55~+150	$^\circ\text{C}$

Thermal Resistance			
Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	R_{thJC}	0.65	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Ambient	R_{thJA}	62	

Specifications T _J = 25°C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	60	--	--	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 60V, V _{GS} = 0V, T _J = 25°C	--	--	1	μA
Gate-Source Leakage	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V	--	--	±100	nA
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	2.0	--	4.0	V
Drain-Source On-Resistance (Note3)	R _{DS(on)}	V _{GS} = 10V, I _D =60A	--	0.007	0.008	Ω
Forward Transconductance	gfs	V _{DS} = 25V, I _D = 60A	--	17	--	S
Dynamic						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = 25V, f = 1.0MHz	--	2699	--	pF
Output Capacitance	C _{oss}		--	1016	--	
Reverse Transfer Capacitance	C _{rss}		--	487	--	
Total Gate Charge	Q _g	V _{DS} =28V, V _{GS} = 15V, I _D =42A	--	115	--	nC
Gate-Source Charge	Q _{gs}		--	13	--	
Gate-Drain Charge	Q _{gd}		--	55	--	
Turn-on Delay Time	t _{d(on)}	V _{DD} = 28V, I _D = 42A, V _{GS} =15V.R _G = 25Ω	--	52	--	ns
Turn-on Rise Time	t _r		--	142	--	
Turn-off Delay Time	t _{d(off)}		--	355	--	
Turn-off Fall Time	t _f		--	230	--	
Drain-Source Body Diode Characteristics						
Continuous Source Current	I _{SD}	T _J = 25°C, I _{SD} = 60A, V _{GS} = 0V	--	--	110	A
Pulsed Source Current	I _{SM}		--	--	440	
Body Forward Voltage	V _{SD}	I _S = 40A, V _{GS} = 0V	--	--	1.2	V
Reverse Recovery Time	t _{rr}	V _{GS} = 0V, I _F = 180A, di _F /dt =100A /μs	--	100	--	ns
Reverse Recovery Charge	Q _{rr}		--	0.33	--	μC

Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. $L=1mH, V_{DD} = 50V, R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$
3. Pulse Test: Pulse width $\leq 300\mu s$, Duty Cycle $\leq 1\%$

Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics ($T_J = 25^\circ\text{C}$)

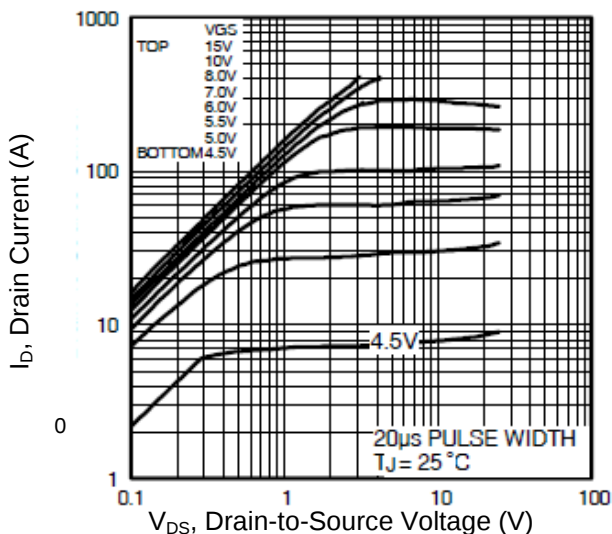


Figure 2. Body Diode Forward Voltage

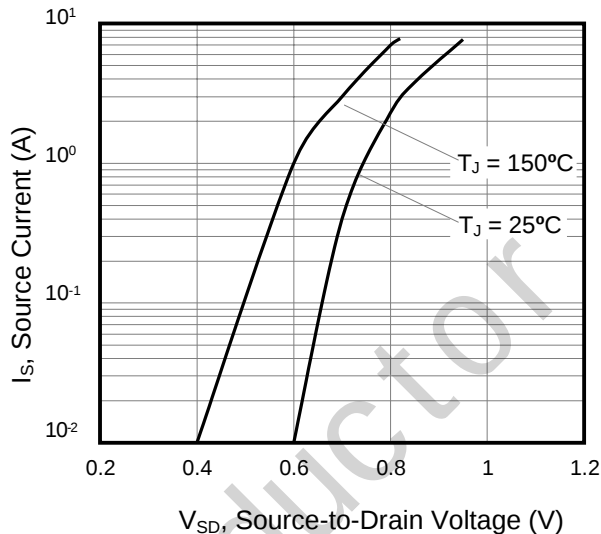


Figure 3. Drain Current vs. Temperature

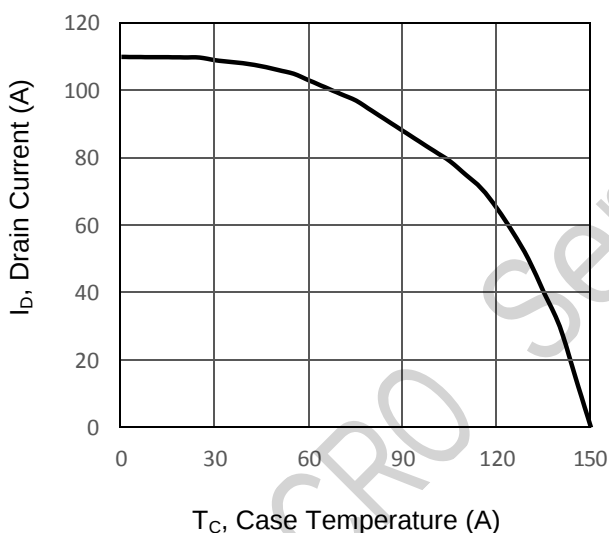


Figure 4. BV_{DSS} Variation vs. Temperature

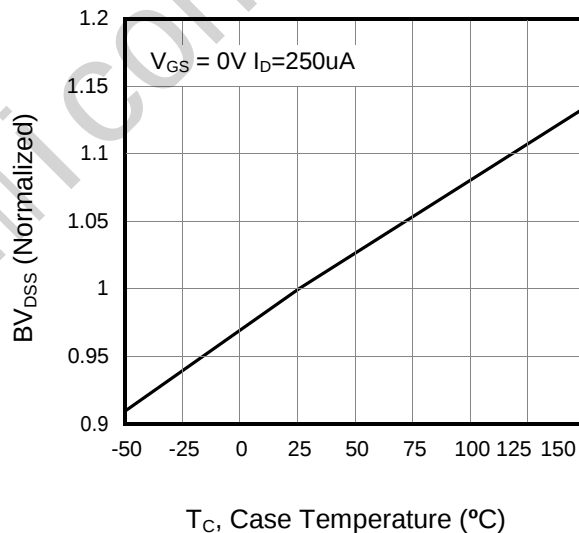


Figure 5. Transfer Characteristics

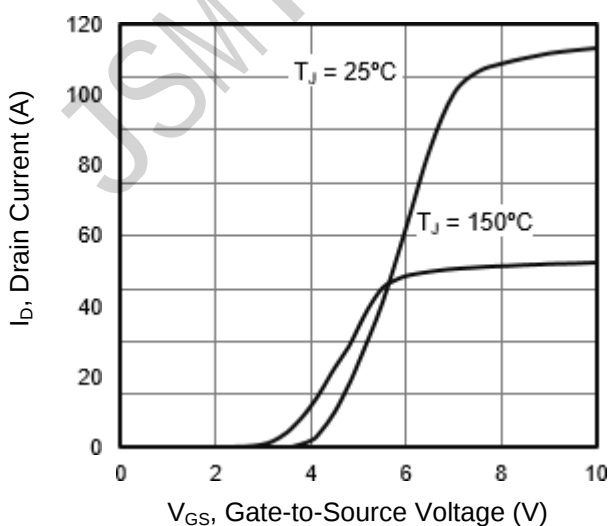
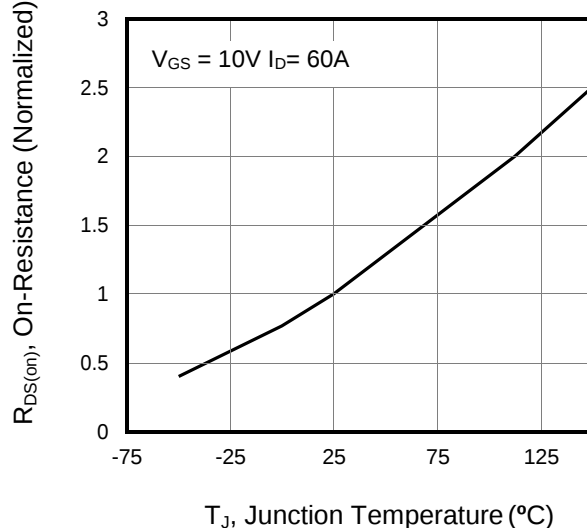


Figure 6. On-Resistance vs. Temperature



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 7. Capacitance

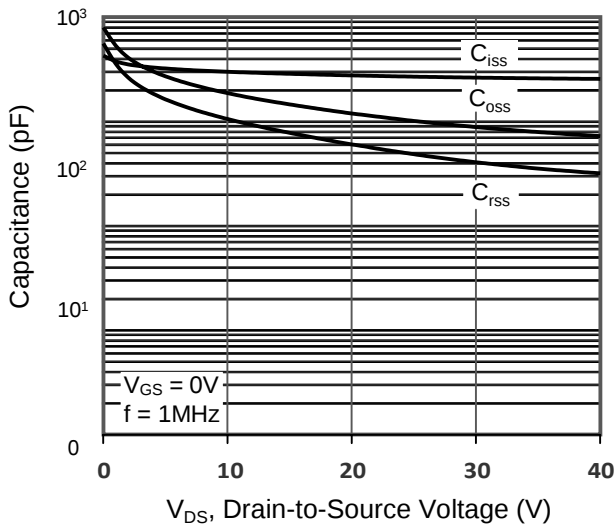


Figure 8. Gate Charge

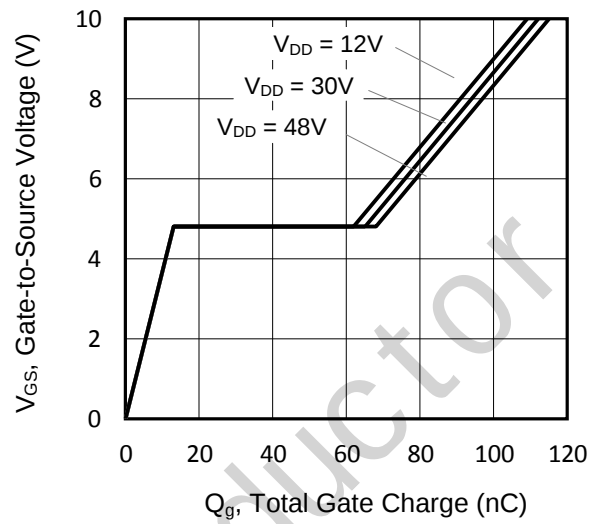


Figure 9. Transient Thermal Impedance
 TO-220

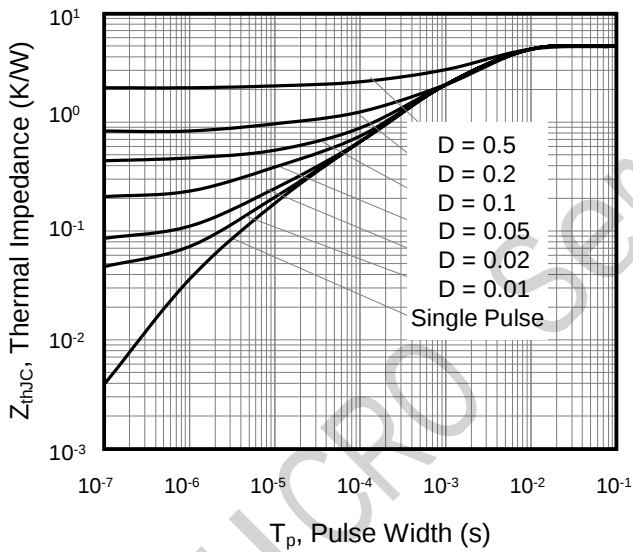


Figure A: Gate Charge Test Circuit and Waveform

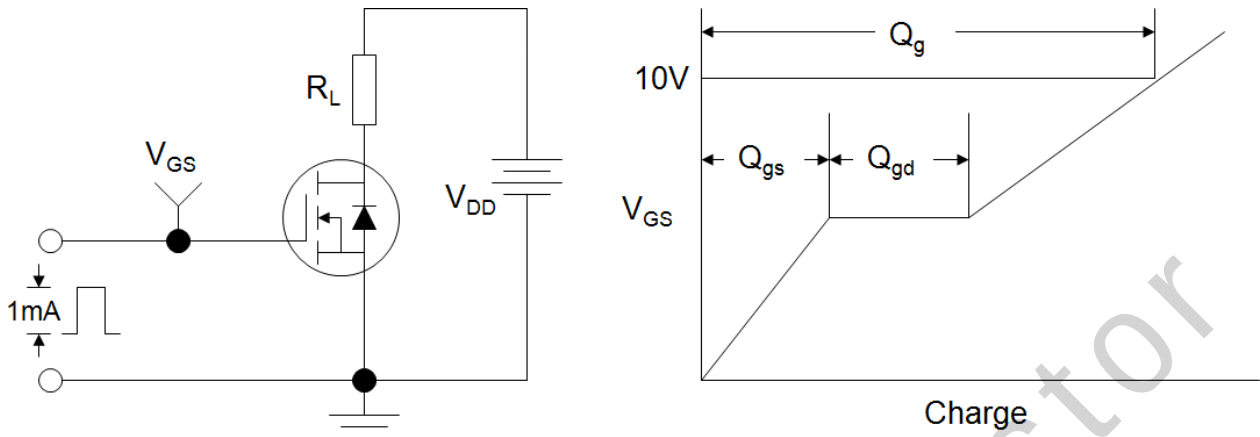


Figure B: Resistive Switching Test Circuit and Waveform

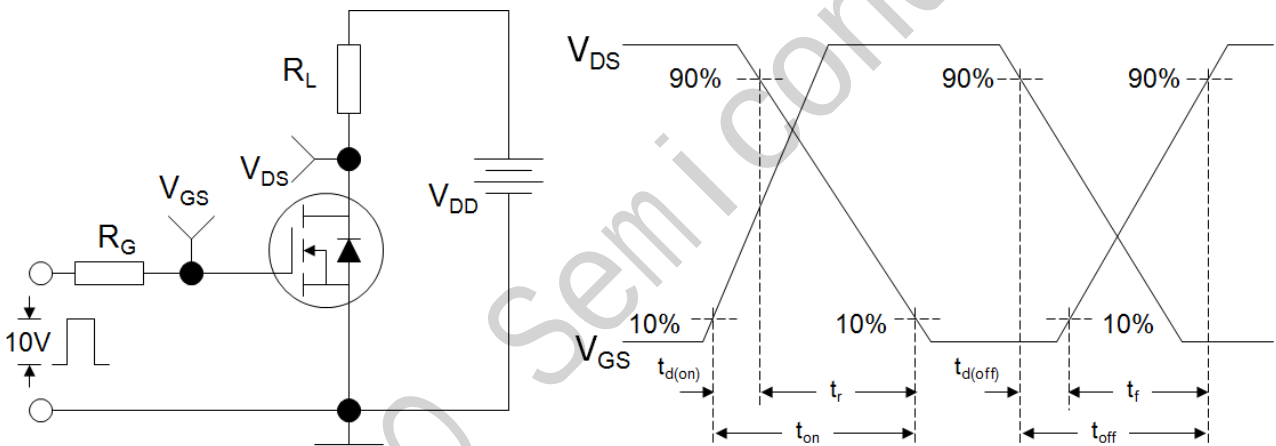
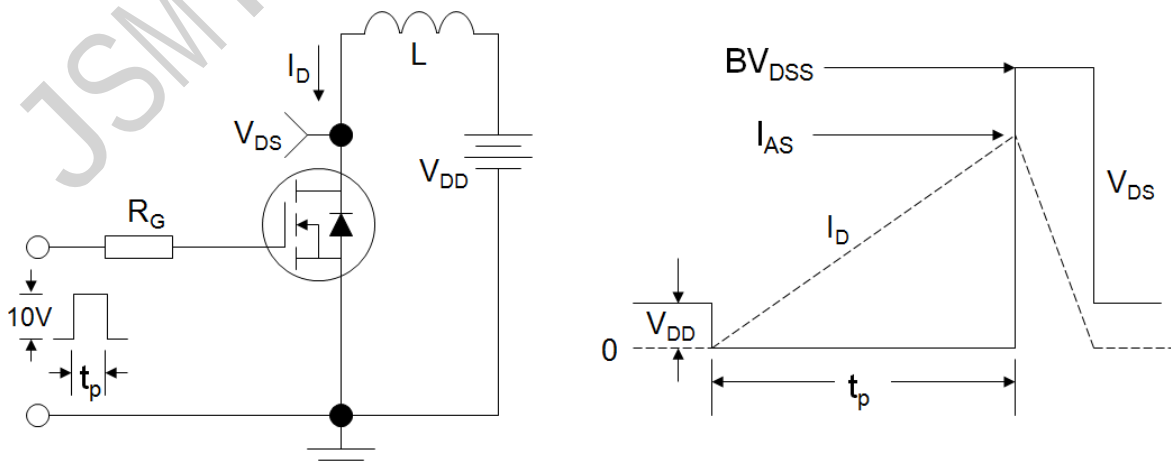


Figure C: Unclamped Inductive Switching Test Circuit and Waveform



外形尺寸图 / Package Dimensions

TO-263

Unit: mm

